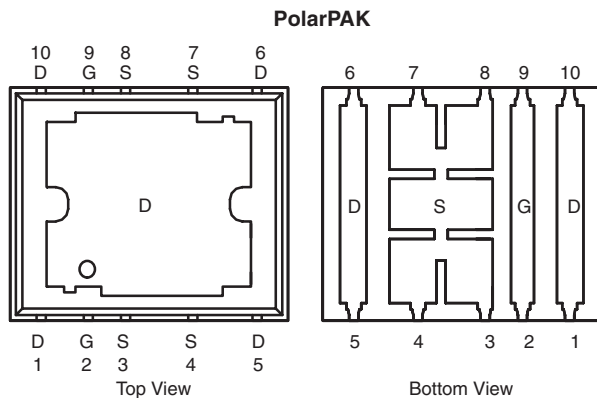


## N-Channel 75-V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω) <sup>e</sup>	I <sub>D</sub> (A) <sup>a</sup>		Q <sub>g</sub> (Typ)
		Silicon Limit	Package Limit	
75	0.0095 at V <sub>GS</sub> = 10 V	79	60	33 nC
	0.0125 at V <sub>GS</sub> = 4.5 V	69	60	

[Package Drawing](#)  
<http://www.vishay.com/doc?72945>



Top surface is connected to pins 1, 5, 6, and 10

**Ordering Information:** SiE818DF-T1-E3 (Lead (Pb)-free)

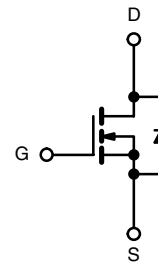
### FEATURES

- TrenchFET<sup>®</sup> Power MOSFET
- Ultra Low Thermal Resistance Using Top-Exposed PolarPAK<sup>®</sup> Package for Double-Sided Cooling
- Leadframe-Based New Encapsulated Package
  - Die Not Exposed
  - Same Layout Regardless of Die Size
- Low Q<sub>gd</sub>/Q<sub>gs</sub> Ratio Helps Prevent Shoot-Through
- 100 % R<sub>g</sub> and UIS Tested



### APPLICATIONS

- Primary Side Switch
- Half-Bridge
- Synchronous Rectification



N-Channel MOSFET

[For Related Documents](#)

<http://www.vishay.com/ppg?74337>

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	75	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	79 (Silicon Limit)	A
		T <sub>C</sub> = 70 °C	60 <sup>a</sup> (Package Limit)	
		T <sub>A</sub> = 25 °C	60 <sup>a</sup>	
		T <sub>A</sub> = 70 °C	16 <sup>b, c</sup>	
Pulsed Drain Current	I <sub>DM</sub>	80		
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	60 <sup>a</sup>	
		T <sub>A</sub> = 25 °C	4.3 <sup>b, c</sup>	
Single Pulse Avalanche Current	I <sub>AS</sub>	50		
Avalanche Energy	E <sub>AS</sub>	125	mJ	
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	125	W
		T <sub>C</sub> = 70 °C	80	
		T <sub>A</sub> = 25 °C	5.2 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	3.3 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 50 to 150		°C
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>		260		

Notes:

a. Package limited.

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 10 sec.

d. See Solder Profile (<http://www.vishay.com/doc?73257>). The PolarPAK is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a, b</sup>	$t \leq 10$ sec	$R_{thJA}$	20	24	°C/W
Maximum Junction-to-Case (Drain Top)	Steady State	$R_{thJC}$ (Drain)	0.8	1	
Maximum Junction-to-Case (Source) <sup>a, c</sup>		$R_{thJC}$ (Source)	2.2	2.7	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. Maximum under Steady State conditions is 68 °C/W.

c. Measured at source pin (on the side of the package).

SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0$ V, $I_D = 250$ $\mu$ A	75			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250$ $\mu$ A		78		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		- 7.1			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250$ $\mu$ A	1.5	2.1	3	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0$ V, $V_{GS} = \pm 20$ V			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 75$ V, $V_{GS} = 0$ V			1	$\mu$ A
		$V_{DS} = 75$ V, $V_{GS} = 0$ V, $T_J = 55$ °C			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5$ V, $V_{GS} = 10$ V	25			A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 16$ A		0.0078	0.0095	$\Omega$
		$V_{GS} = 4.5$ V, $I_D = 14$ A		0.0103	0.0125	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 20$ V, $I_D = 16$ A		50		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 38$ V, $V_{GS} = 0$ V, $f = 1$ MHz		3200		pF
Output Capacitance	$C_{oss}$		330			
Reverse Transfer Capacitance	$C_{rss}$		170			
Total Gate Charge	$Q_g$	$V_{DS} = 38$ V, $V_{GS} = 10$ V, $I_D = 16$ A		63	95	nC
		$V_{DS} = 38$ V, $V_{GS} = 4.5$ V, $I_D = 16$ A		33	50	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 38$ V, $V_{GS} = 4.5$ V, $I_D = 16$ A		11		nC
Gate-Drain Charge	$Q_{gd}$		17			
Gate Resistance	$R_g$		$f = 1$ MHz	0.95	1.5	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 38$ V, $R_L = 3.8$ $\Omega$ $I_D \cong 10$ A, $V_{GEN} = 4.5$ V, $R_g = 1$ $\Omega$		30	45	ns
Rise Time	$t_r$		150	225		
Turn-Off Delay Time	$t_{d(off)}$		40	60		
Fall Time	$t_f$		15	25		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 38$ V, $R_L = 3.8$ $\Omega$ $I_D \cong 10$ A, $V_{GEN} = 10$ V, $R_g = 1$ $\Omega$		15	25	
Rise Time	$t_r$		15	25		
Turn-Off Delay Time	$t_{d(off)}$		40	60		
Fall Time	$t_f$		10	15		
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25$ °C			60	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				80	
Body Diode Voltage	$V_{SD}$	$I_S = 10$ A		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 10$ A, $di/dt = 100$ A/ $\mu$ s, $T_J = 25$ °C		100	150	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		345	520	nC	
Reverse Recovery Fall Time	$t_a$		75		ns	
Reverse Recovery Rise Time	$t_b$		25			

Notes:

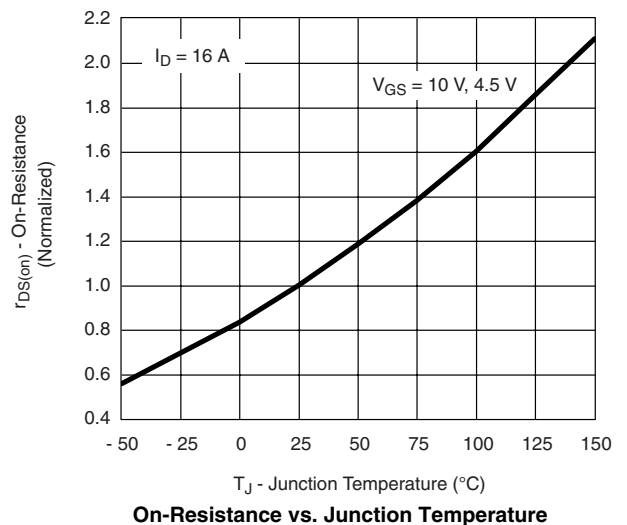
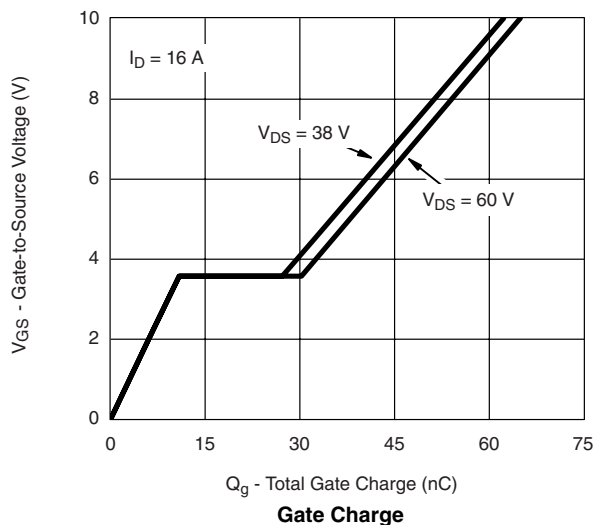
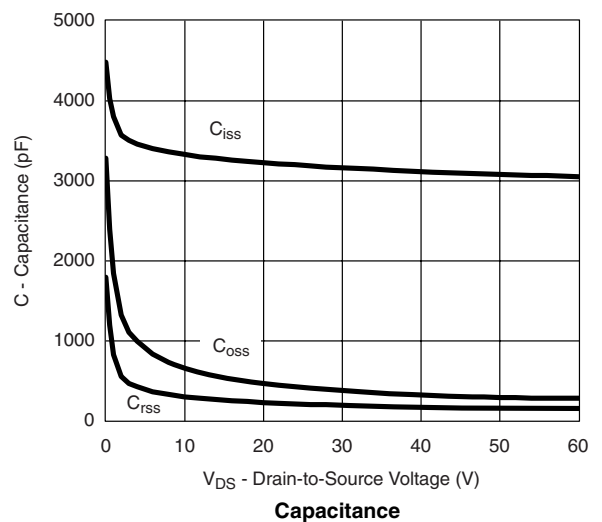
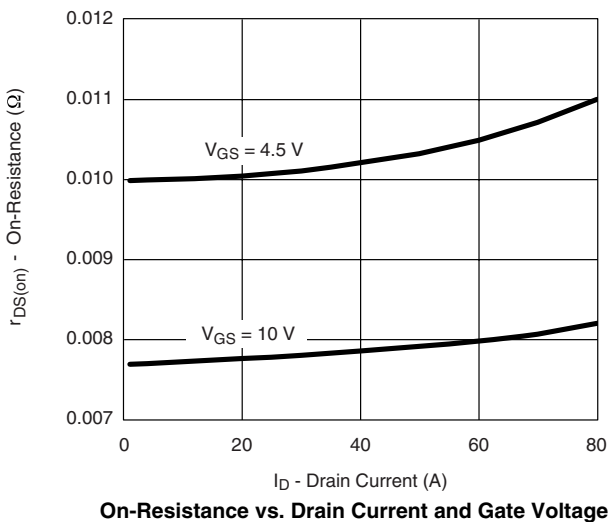
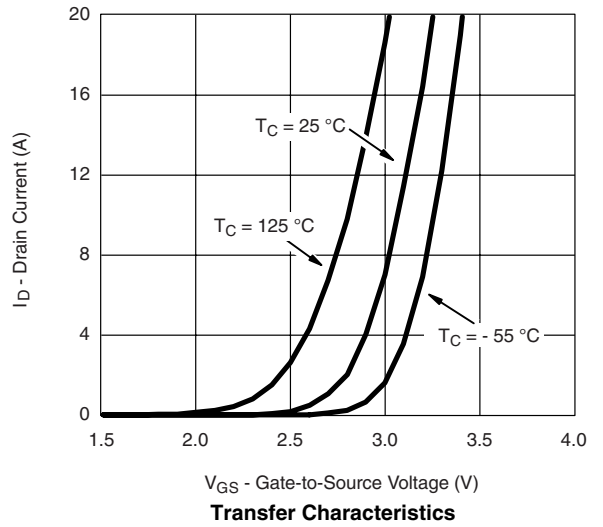
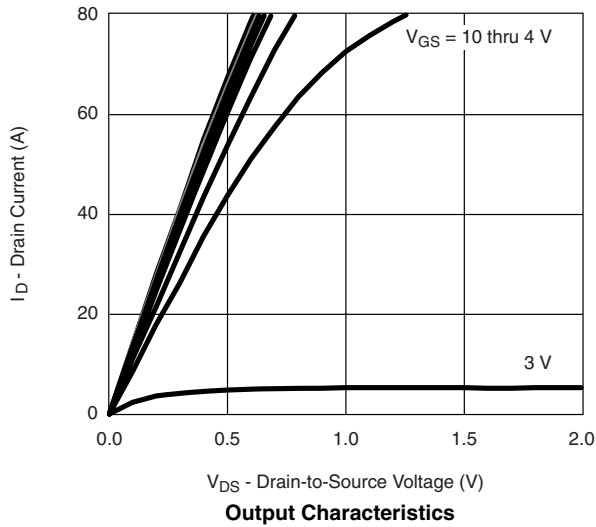
a. Pulse test; pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2$  %

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.

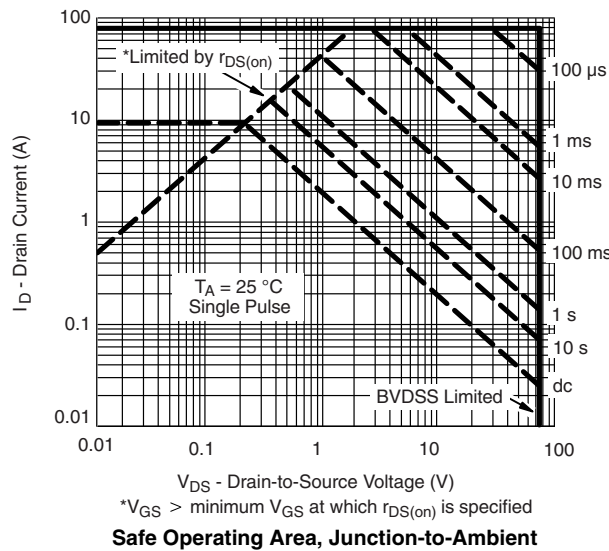
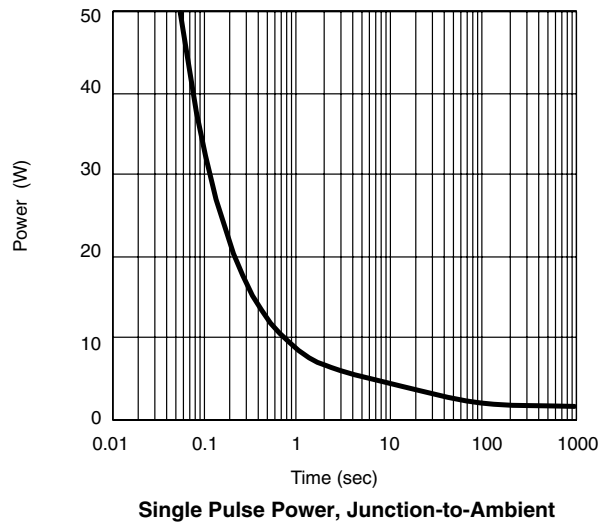
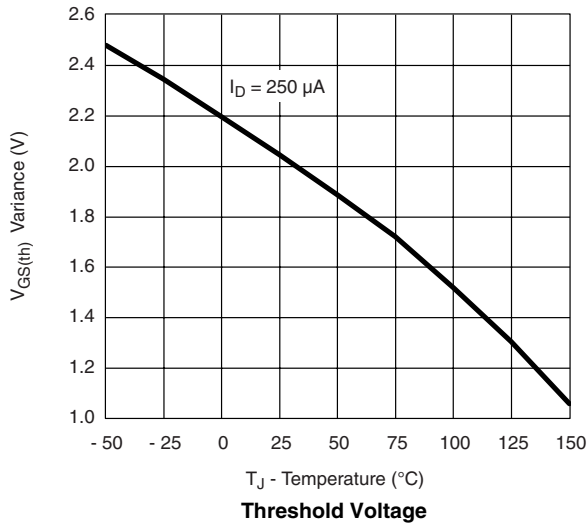
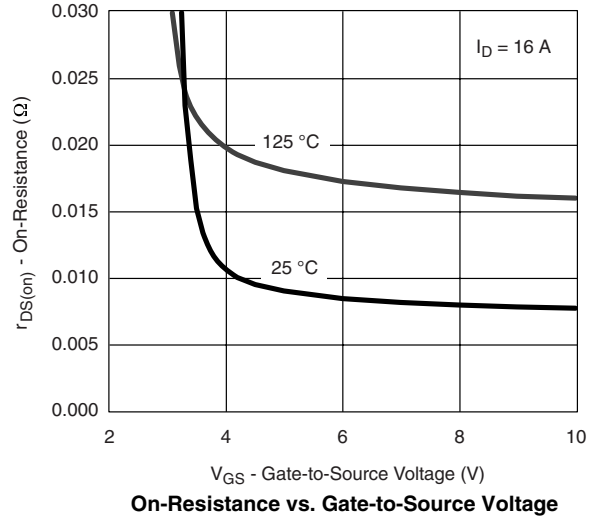
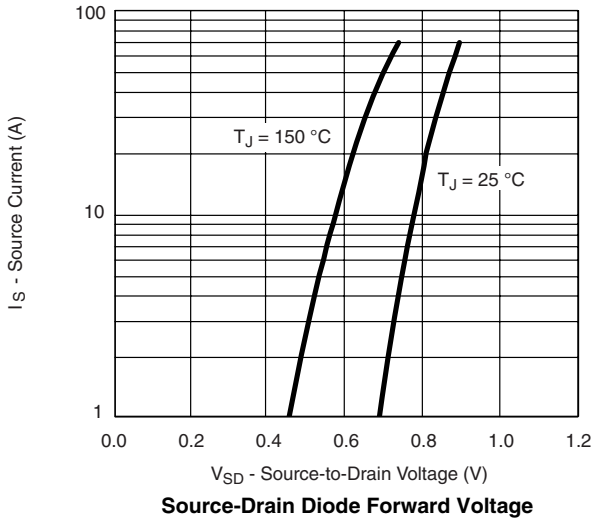


**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



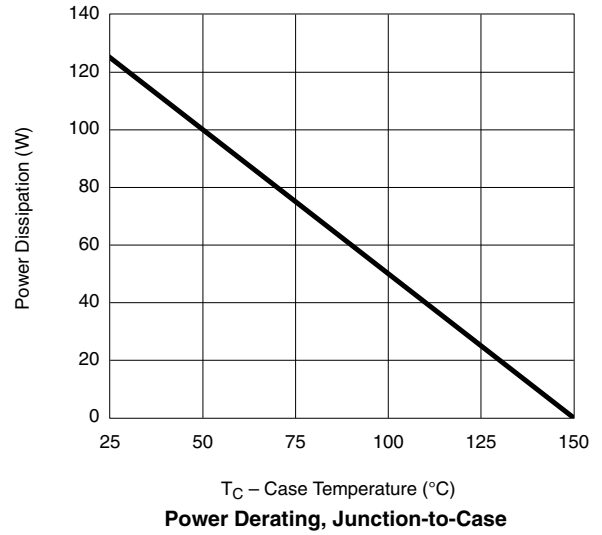
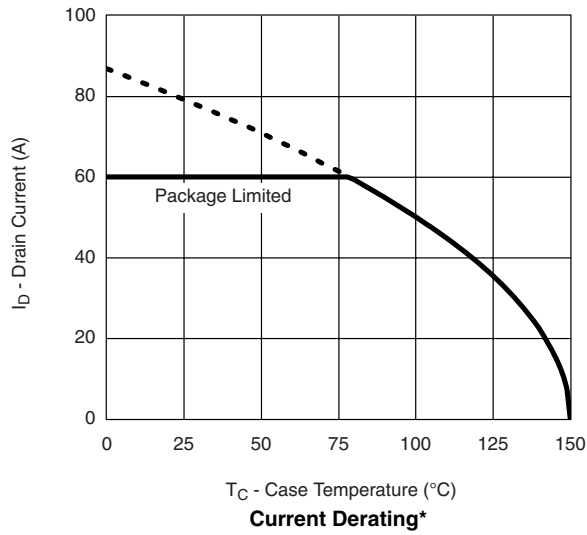


**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted





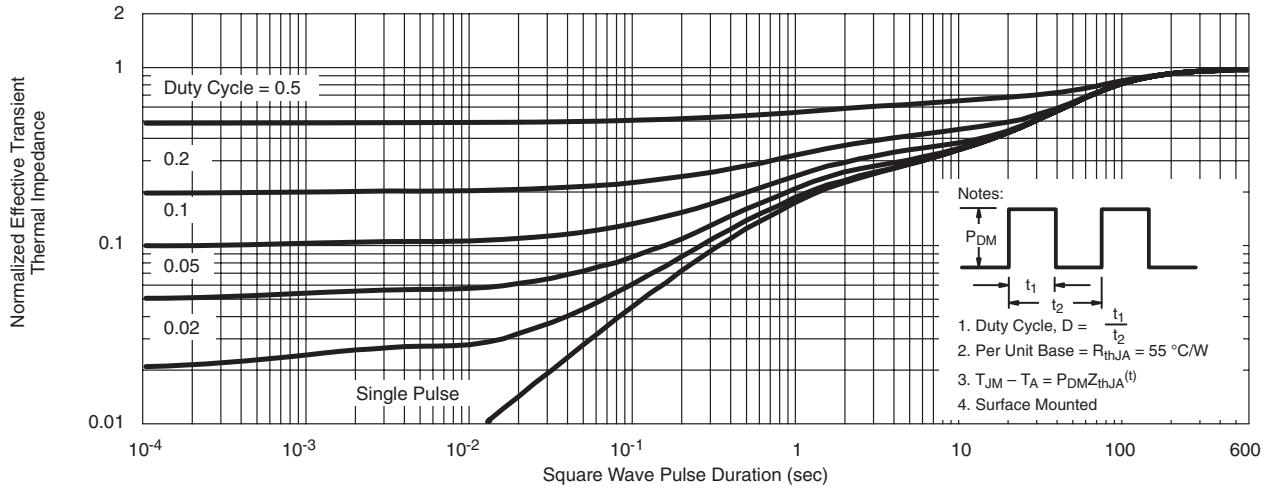
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



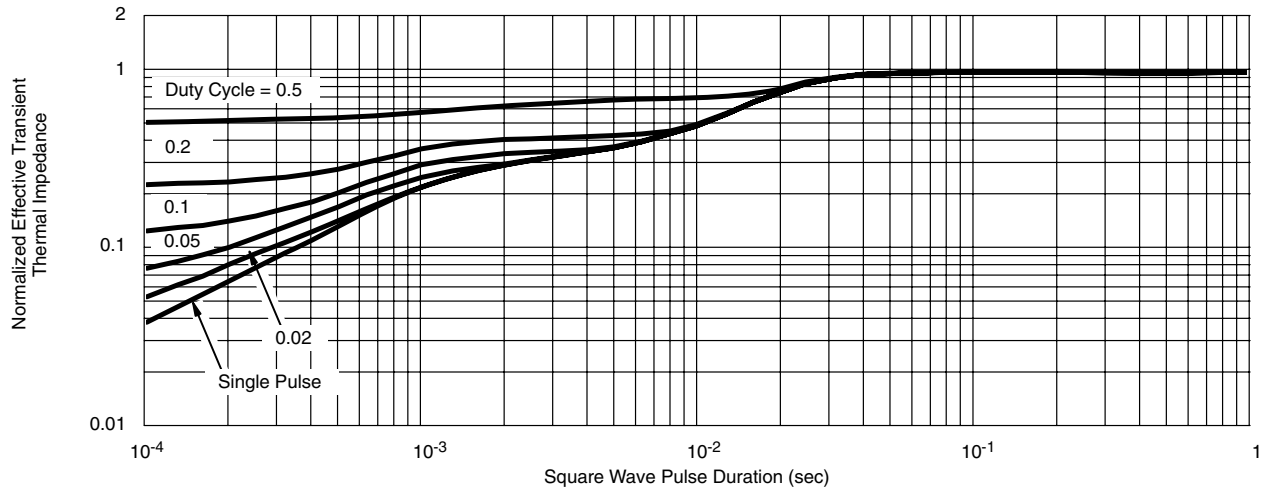
\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



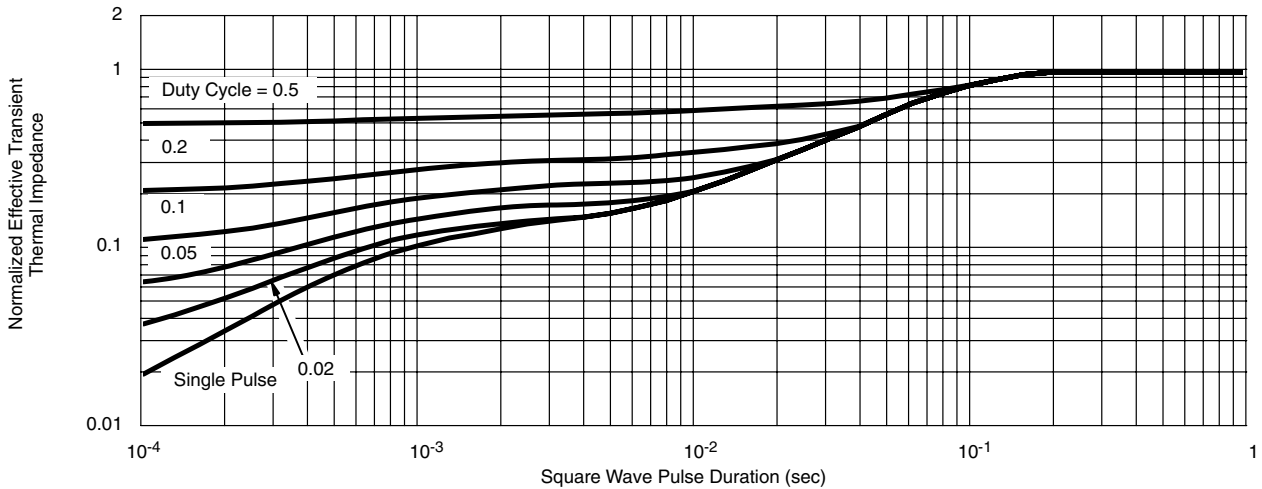
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Case (Drain Top)**



**Normalized Thermal Transient Impedance, Junction-to-Source**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?74485>.



## Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.